

Characterization of single-cycle THz pulses at the CTR source at FLASH

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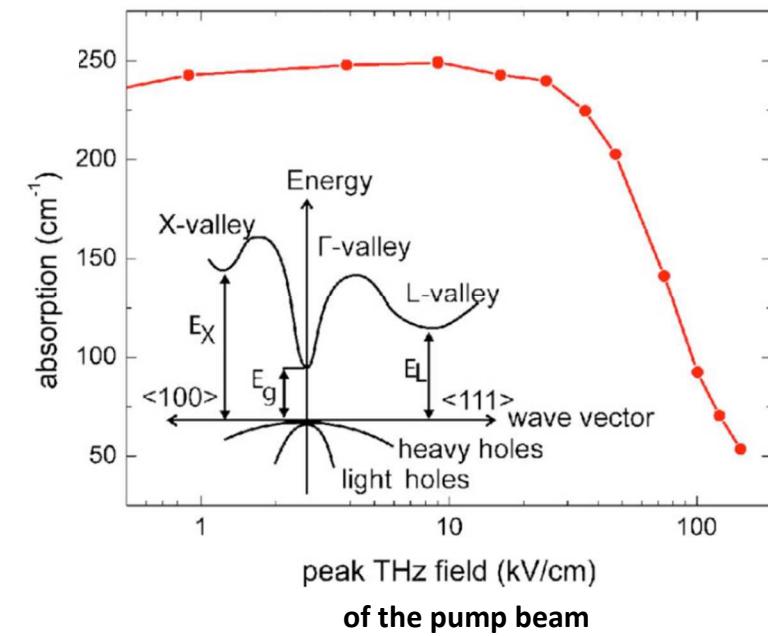
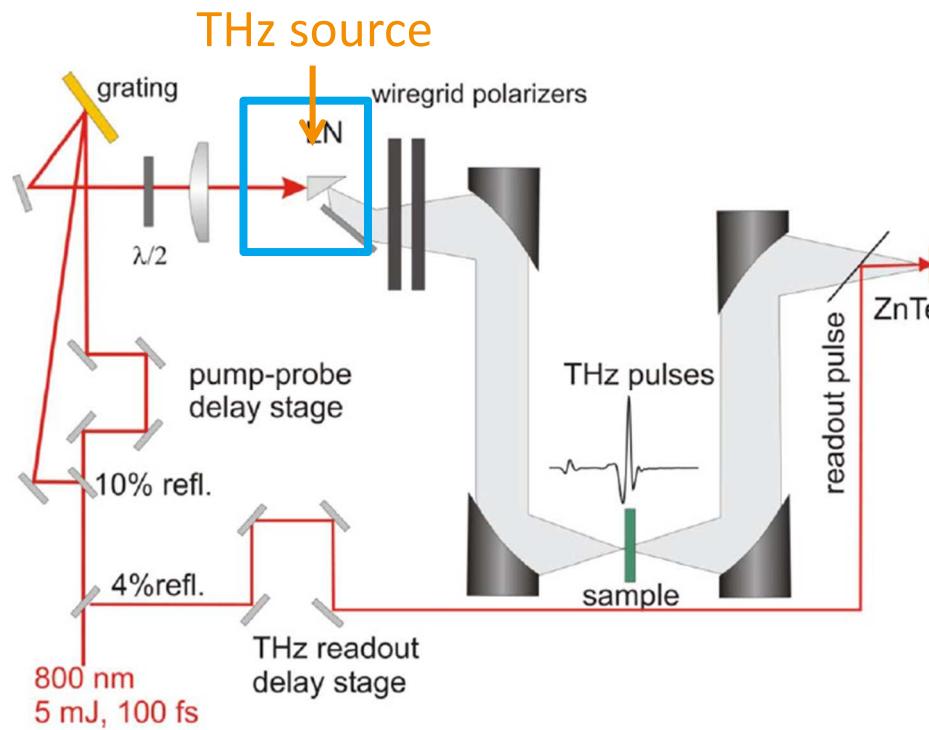
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Introduction

» THz pump / THz probe of semiconductors

$1 \text{ THz} \hat{=} 300 \mu\text{m} \hat{=} 4.1 \text{ meV} \Rightarrow$ mobility of free carriers in n-type GaAs

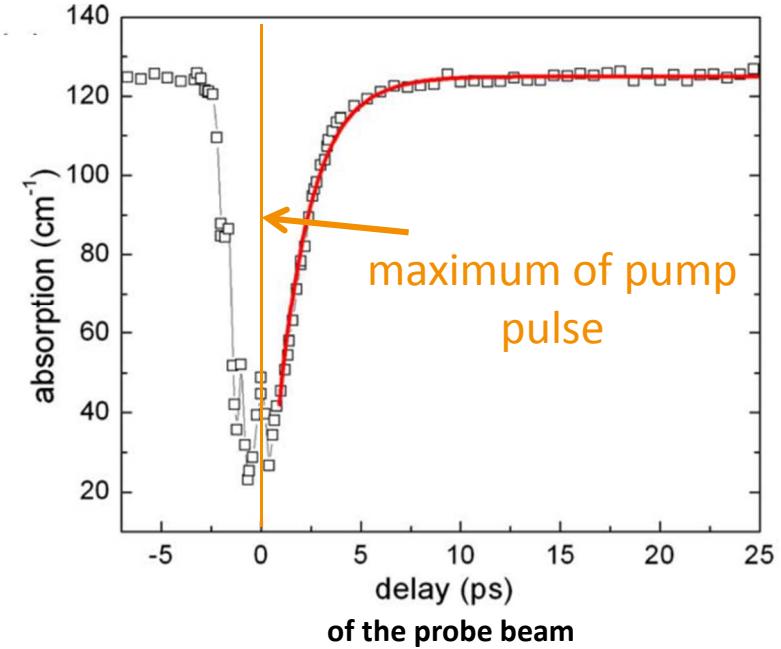
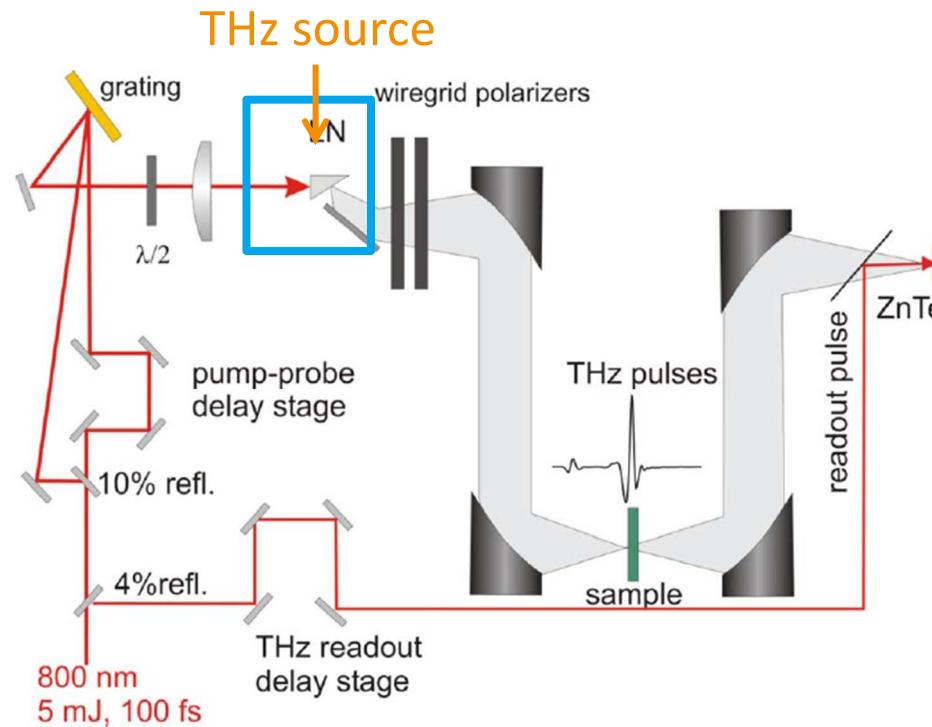


[1] (all)

Introduction

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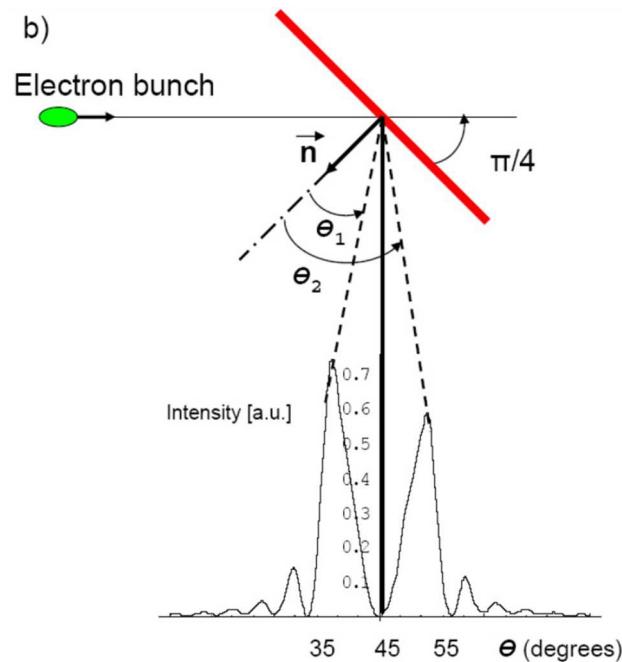
Introduction

- Pulsed THz sources
 - » photoconductive switches
 - » optical rectification
 - » free-electron laser
 - » undulator radiation
 - » coherent transition radiation
- 
- laser-driven
- accelerator-driven

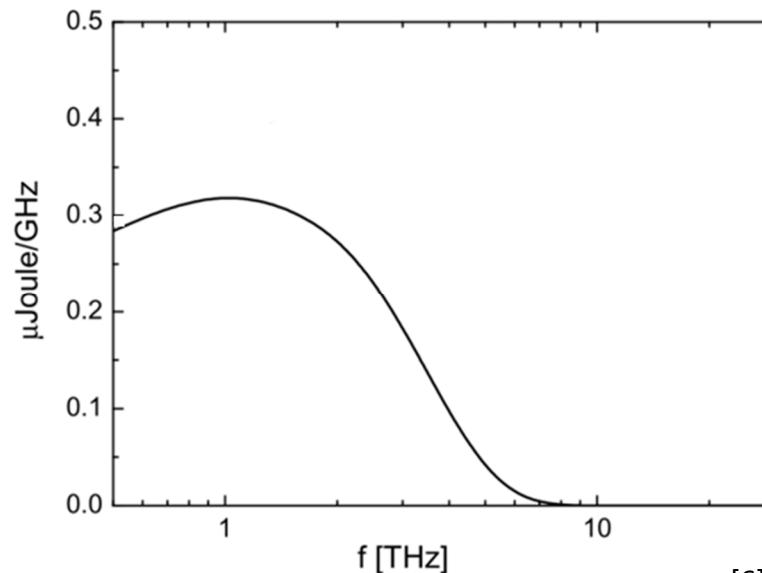
Background

- Coherent transition radiation (CTR)

- » angular distribution in the far field
intensity maximum at $\theta = \gamma^{-1}$



- » spectrum (Gaussian bunch):



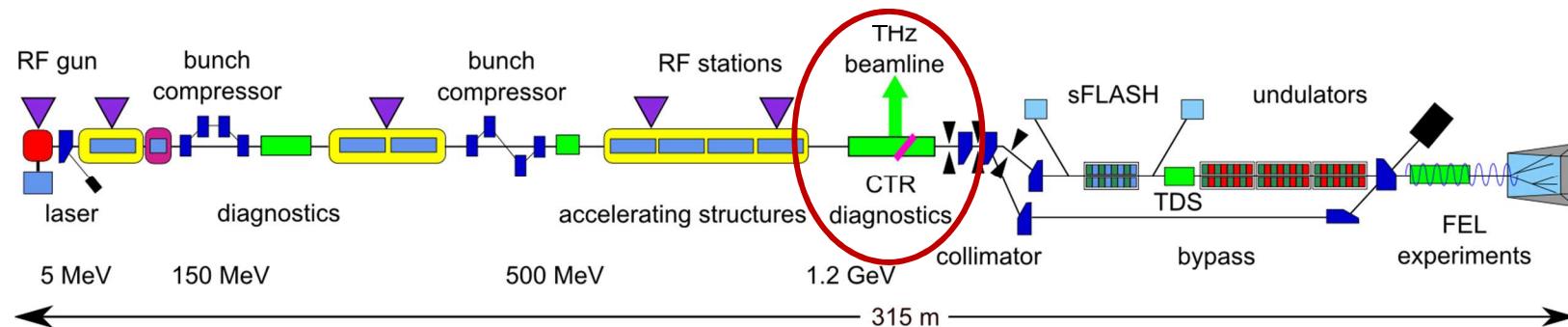
[6] (all)

far field $D > \gamma^2 \lambda$

$\gamma = 1000, \lambda = 0.3 \text{ mm} \rightarrow D = 300 \text{ m}$

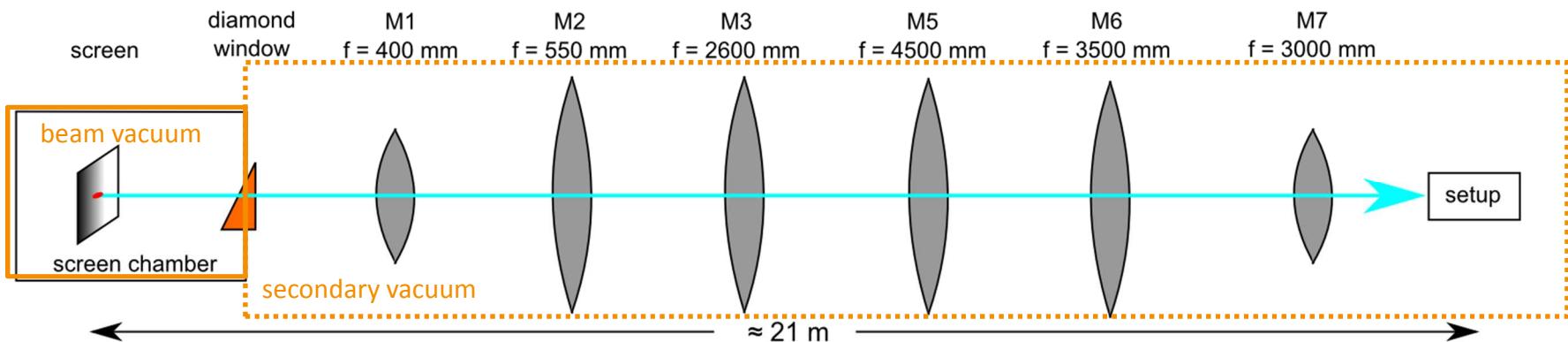
Background

- The THz-beamline at FLASH



screen material: 150 nm aluminum on 380 μm silicon

[7]

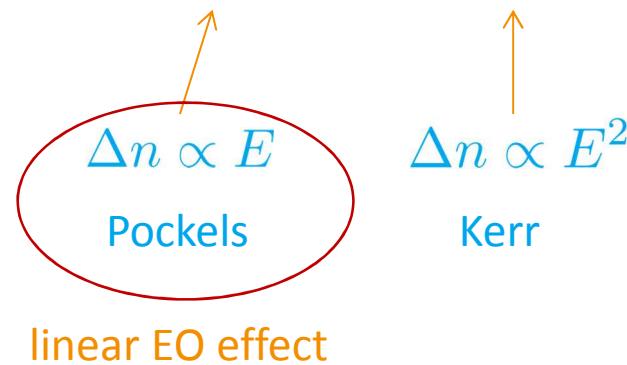


Background

- The electro-optic (EO) effect
polarization induced by an electric field

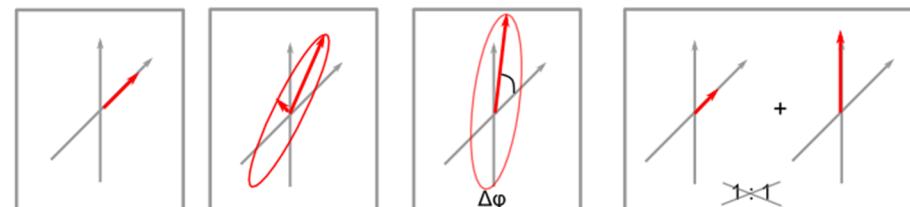
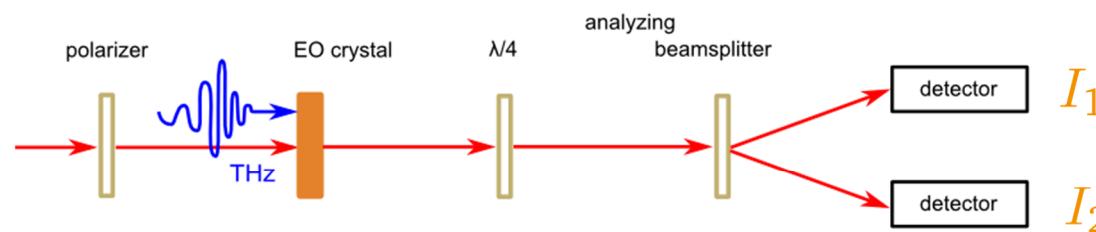
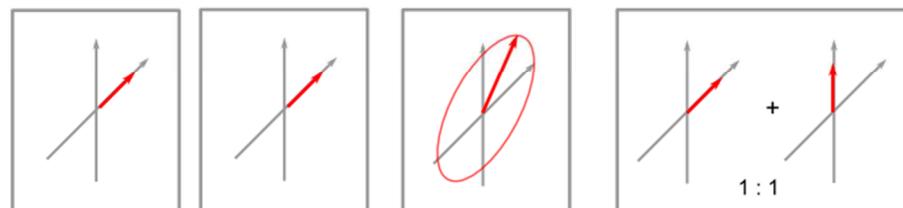
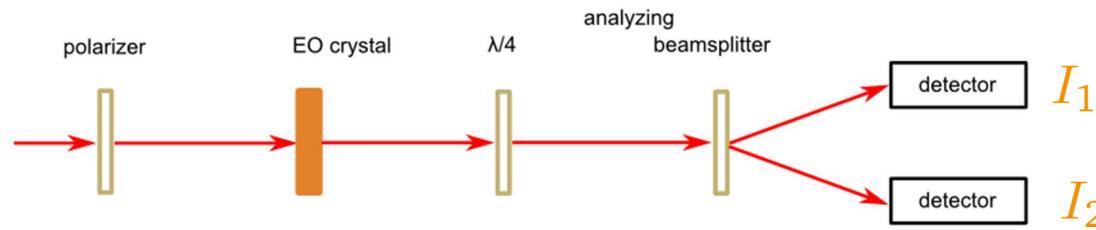
in general: $\vec{P} = \epsilon_0 \chi \vec{E}$

$$= \epsilon_0 \left(\chi_e^{(1)} \vec{E} + \chi_e^{(2)} \vec{E}^2 + \chi_e^{(3)} \vec{E}^3 + \dots \right)$$



[9]

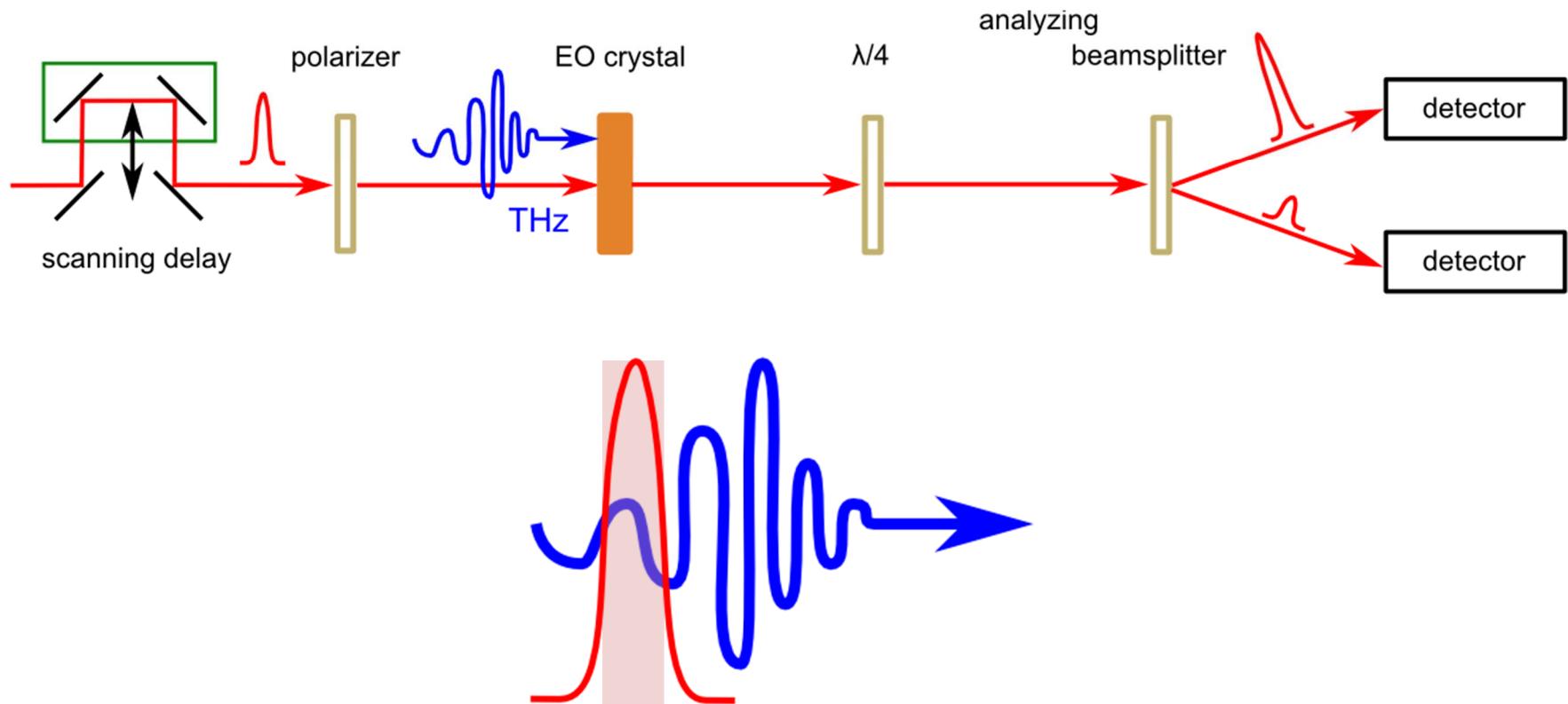
Background



$$\Gamma(\alpha) = \frac{\pi d}{\lambda} n_0^3 E_{\text{THz}} r_{41} \sqrt{1 + 3 \cos^2(\alpha)} = \sin^{-1} \left(\frac{I_1 - I_2}{I_1 + I_2} \right)$$

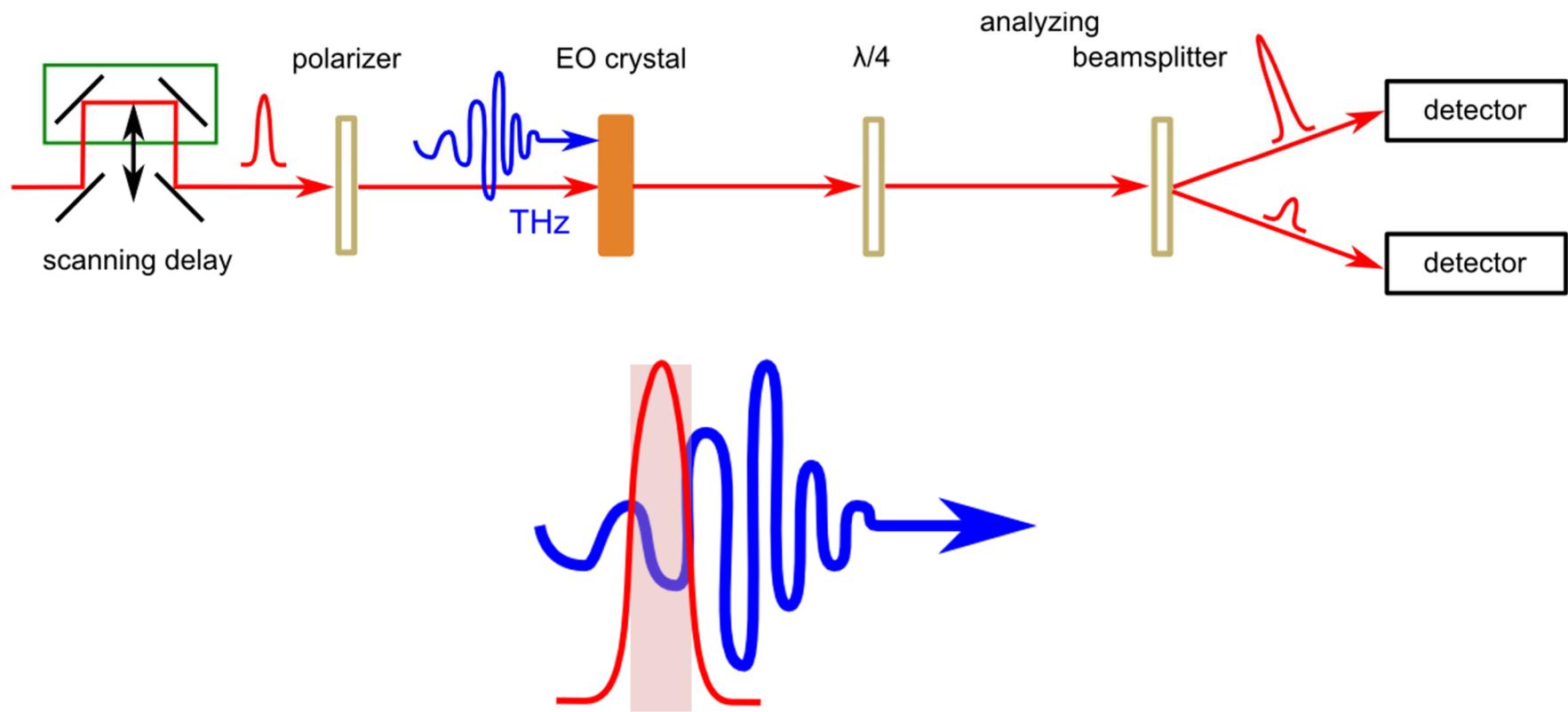
Background

- Sampling



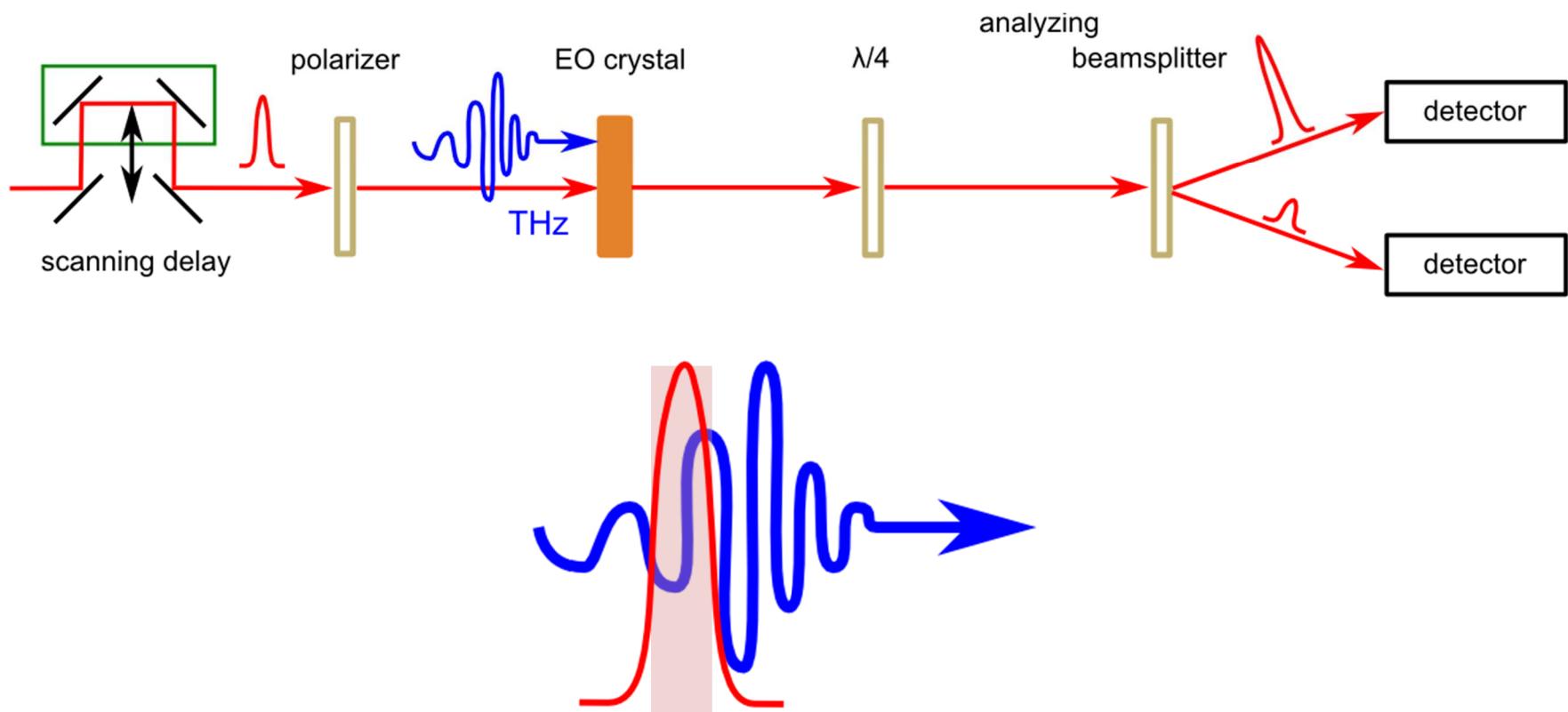
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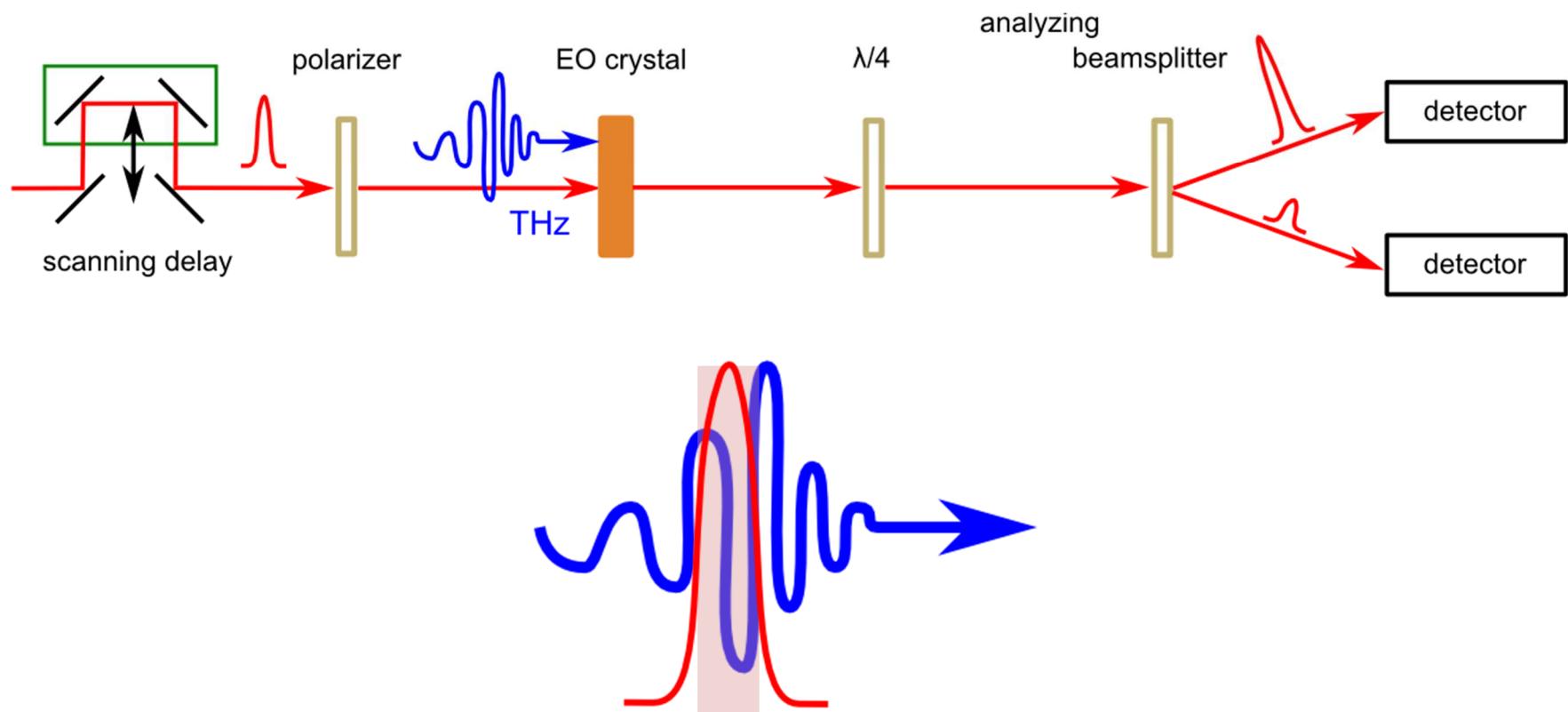
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- Sampling



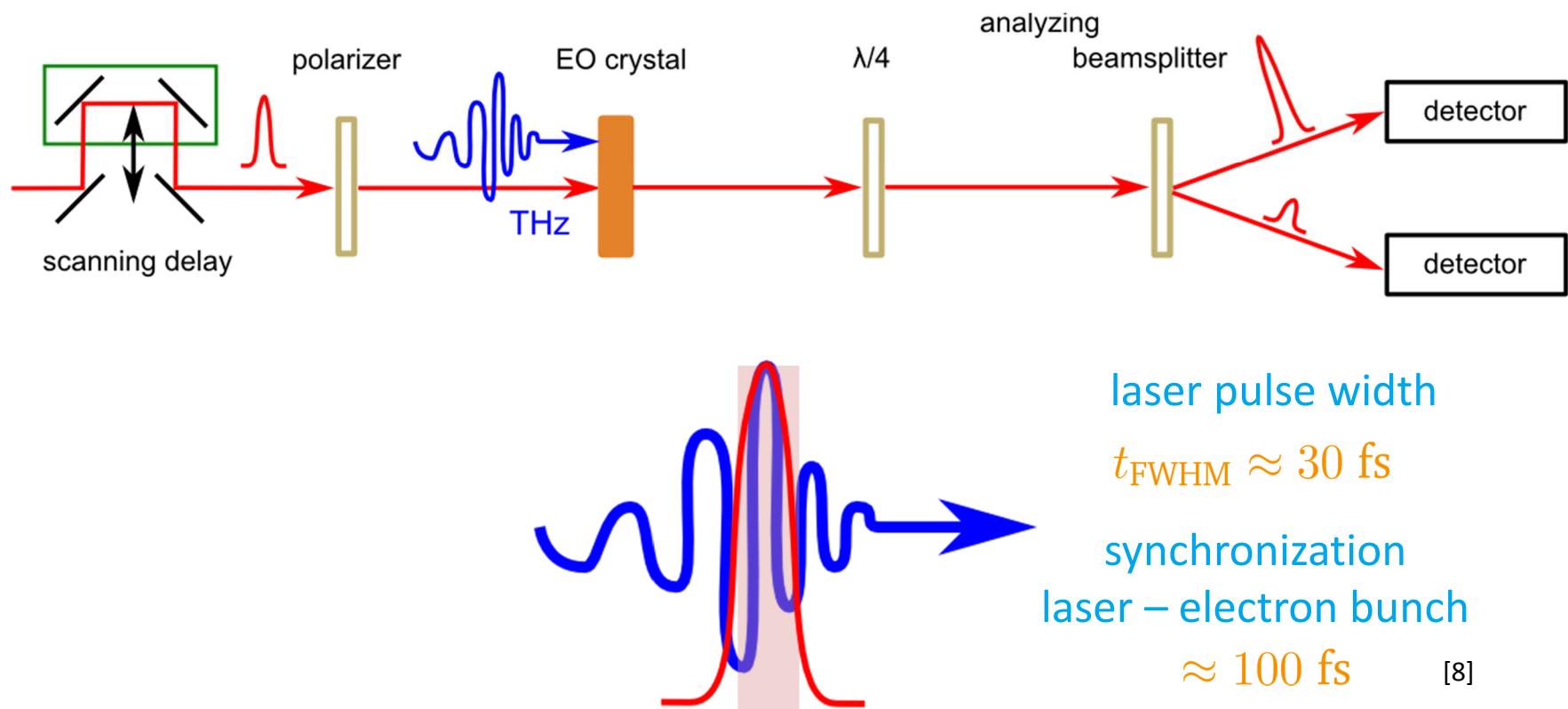
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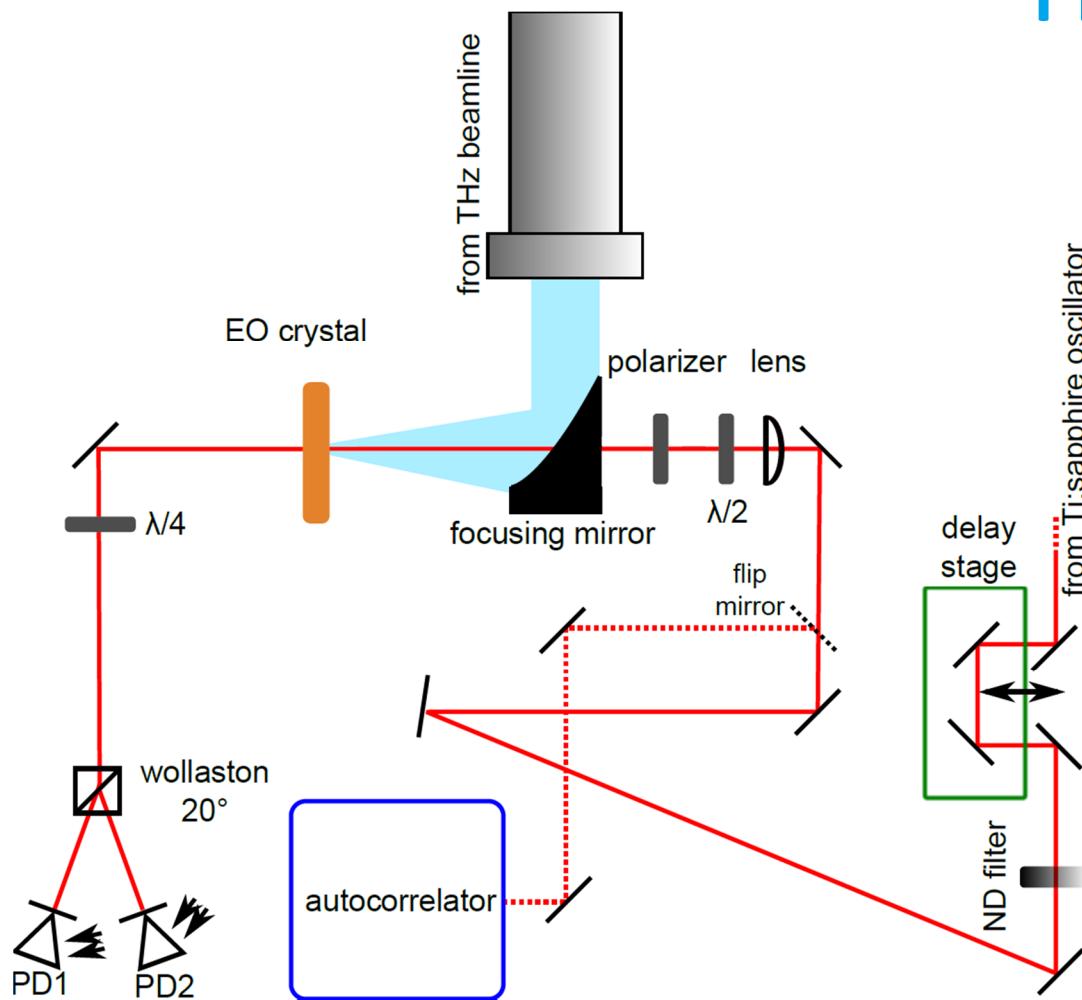


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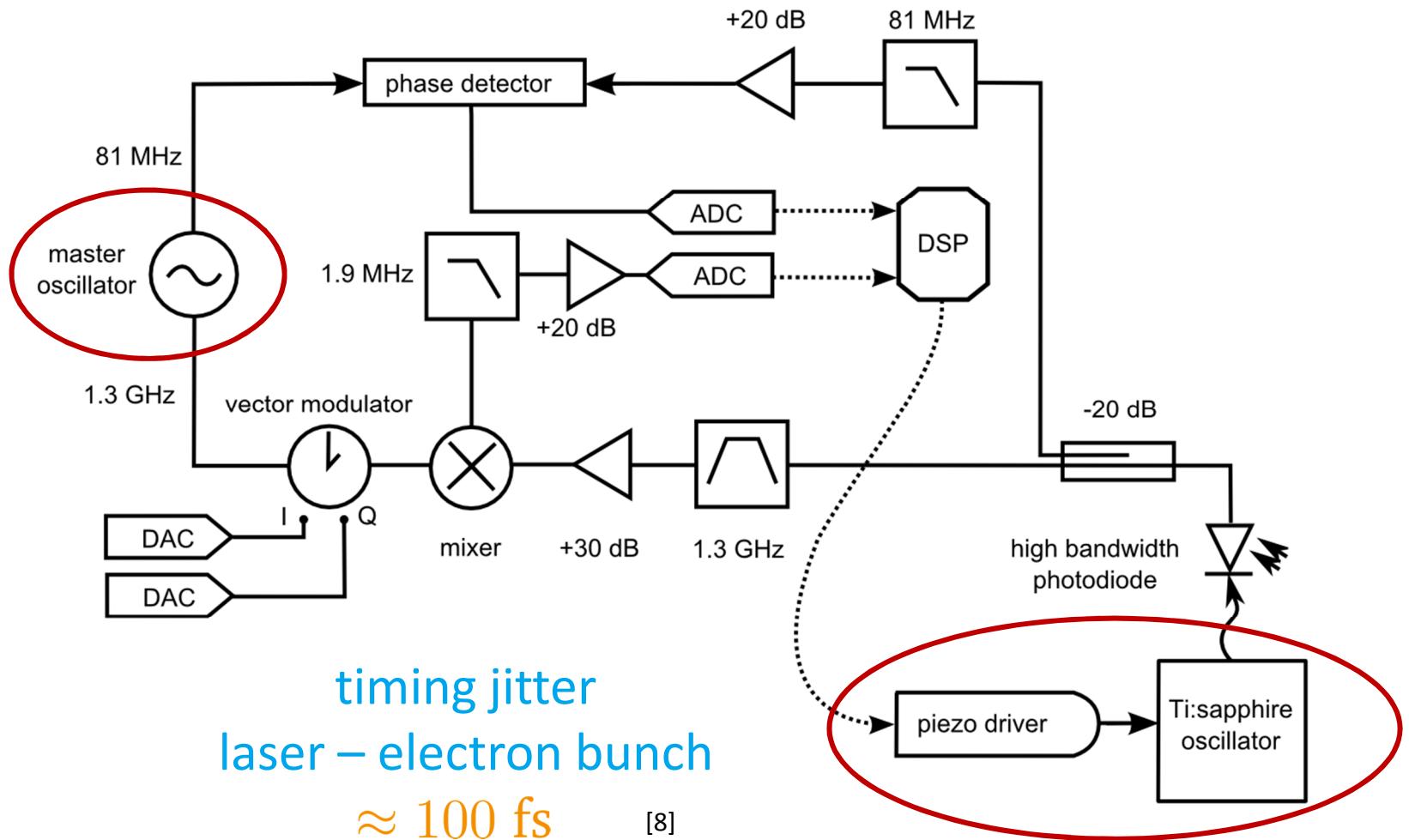


The Experiment



The Experiment

- Synchronization



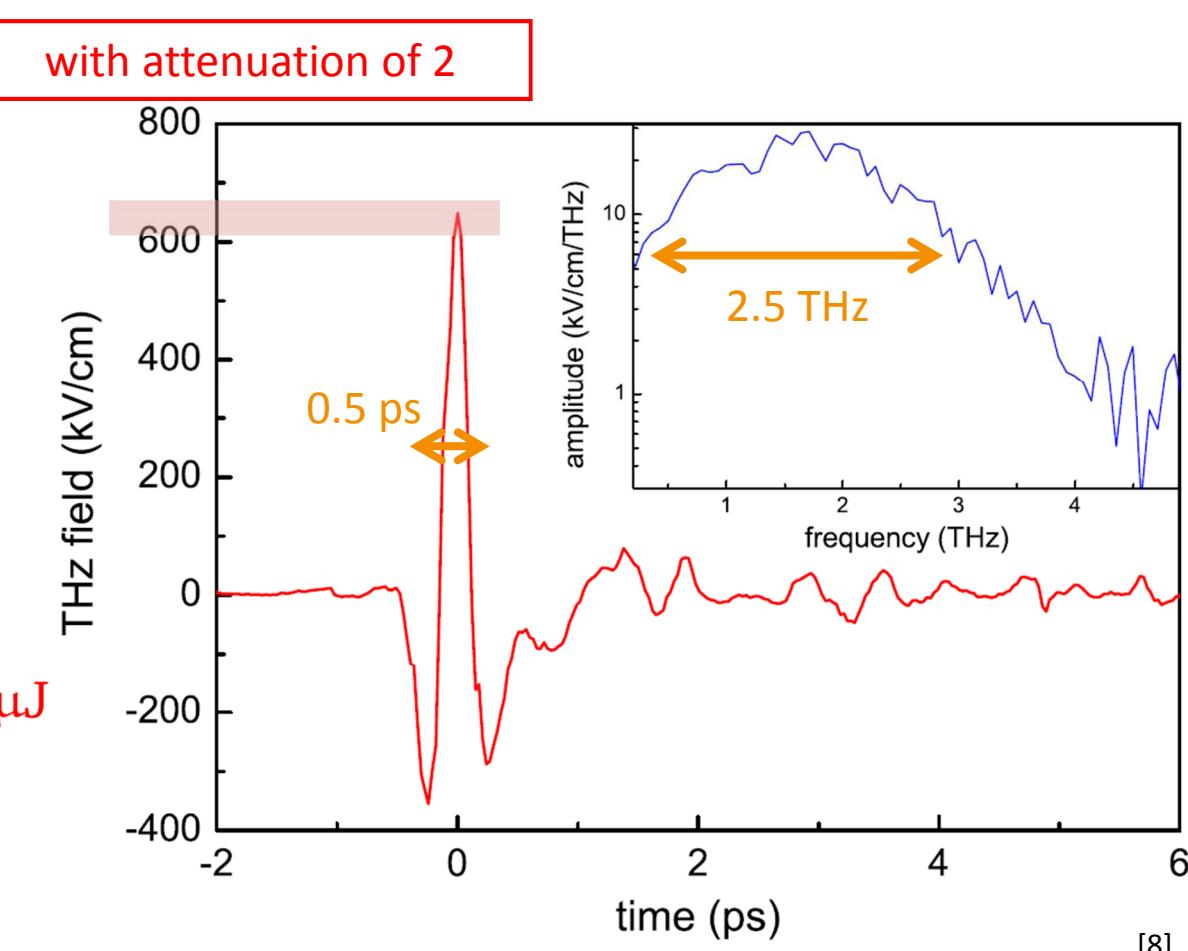
The Experiment

- Results

GaP 0.2 mm
vacuum

SASE parameters
700 MeV
0.6 nC

> 1 MV/cm @ 100 μ J



Outlook

Use CTR source for experiments
for nonlinear optics, material science...

- » Optimization of electron beam parameters for output power
- » Benefit from the laser-based synchronization

Summary

CTR source of THz pulses with world-leading field strengths and bandwidth for various applications

1 MV/cm @ 100 μJ

References and further reading

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